

200V Single N-Channel HEXFET Power MOSFET in a D2-Pak package; Similar to IRF640NS with Lead Free Packaging

Manufacturers	<u>Infineon Technologies Corporation</u>
Package/Case	PAK-3
Product Type	Transistors
RoHS	Green
Lifecycle	



Images are for reference only

Please submit RFQ for IRF640NSPBF or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

[RFQ](#)

## General Description

Fifth Generation HEXFET® Power MOSFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

Advanced Process Technology  
Dynamic dv/dt Rating  
175°C Operating Temperature  
Fast Switching  
Fully Avalanche Rated  
Ease of Paralleling  
Simple Drive Requirements

## Features

Planar cell structure for wide SOA

Optimized for broadest availability from distribution partners

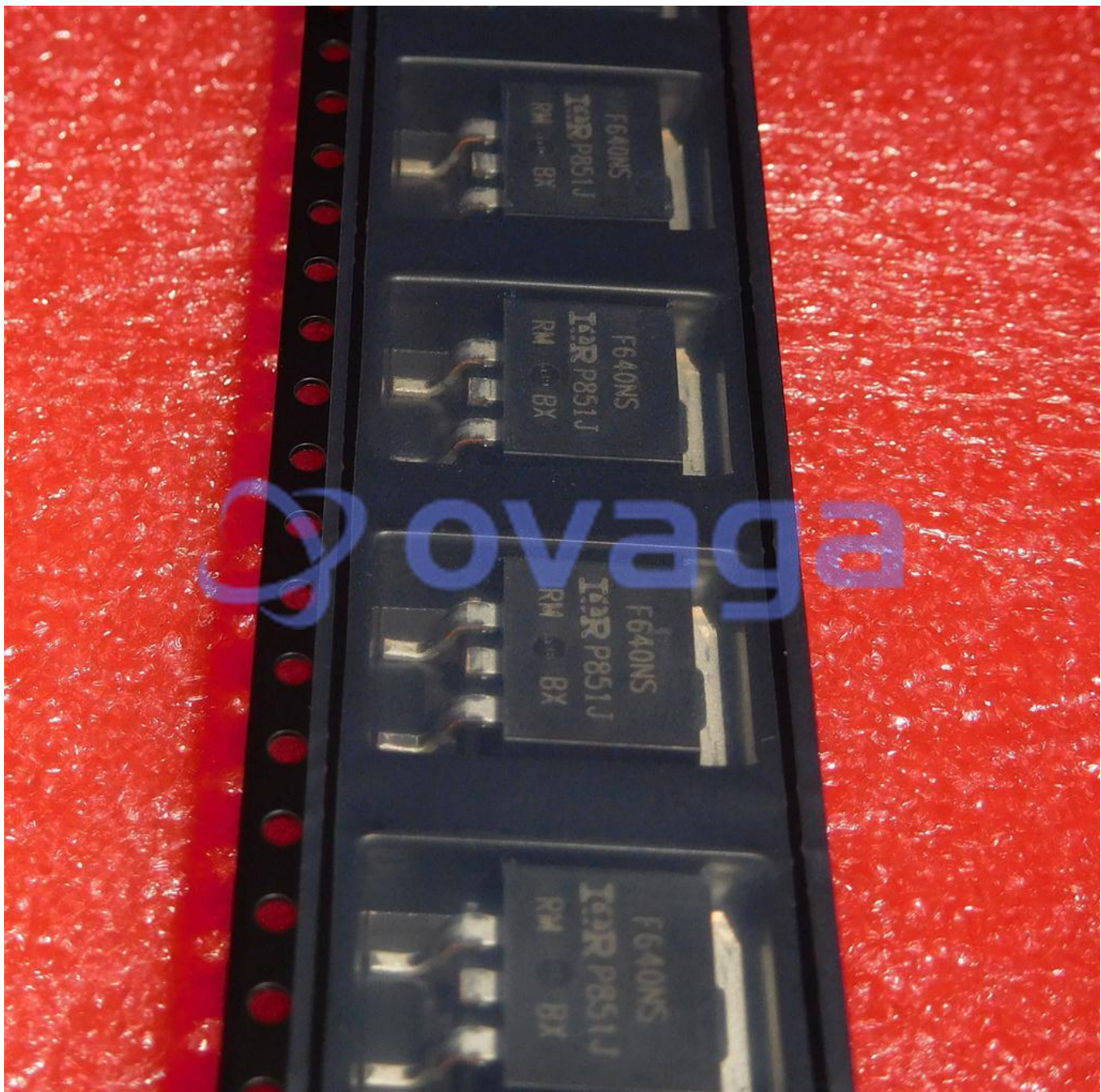
Product qualification according to JEDEC standard

Silicon optimized for applications switching below <100kHz

Industry standard surface-mount power package

High-current carrying capability package (up to 195 A, die-size dependent)

Capable of being wave-soldered



## Related Products



### [IRLTS6342TRPBF](#)

Infineon Technologies Corporation  
TSOP-6



### [IRF9310PBF](#)

Infineon Technologies Corporation  
SOIC-8



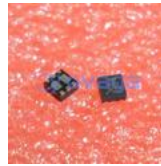
### [IRF9358TRPBF](#)

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SOP-8



### [IRFB3307ZPBF](#)

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TO-220AB



### [IRLHS6376TRPBF](#)

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